

See discussions, stats, and author profiles for this publication at: <https://www.researchgate.net/publication/298734982>

Enhancing Thermoelectric Performance of Bi₂Te₃ -based Nanostructures through Rational Structure Design

Article in *Nanoscale* · March 2016

DOI: 10.1039/C6NR00719H

CITATION

1

READS

76

4 authors:



Min Hong

University of Queensland

16 PUBLICATIONS 79 CITATIONS

SEE PROFILE



Zhi-Gang Chen

University of Southern Queensland

159 PUBLICATIONS 6,783 CITATIONS

SEE PROFILE



Lei Yang

University of Queensland

33 PUBLICATIONS 338 CITATIONS

SEE PROFILE



Jin Zou

University of Queensland

715 PUBLICATIONS 16,172 CITATIONS

SEE PROFILE

Some of the authors of this publication are also working on these related projects:



Developing high-performance thermoelectric materials through nanostructuring and band engineering [View project](#)



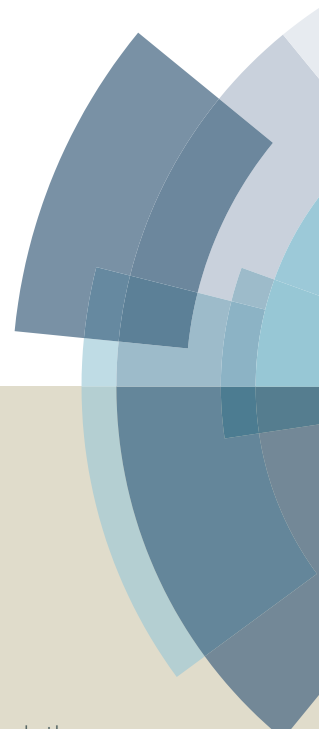
TiO₂ nanotube for gas sensor [View project](#)

All content following this page was uploaded by [Min Hong](#) on 06 April 2016.

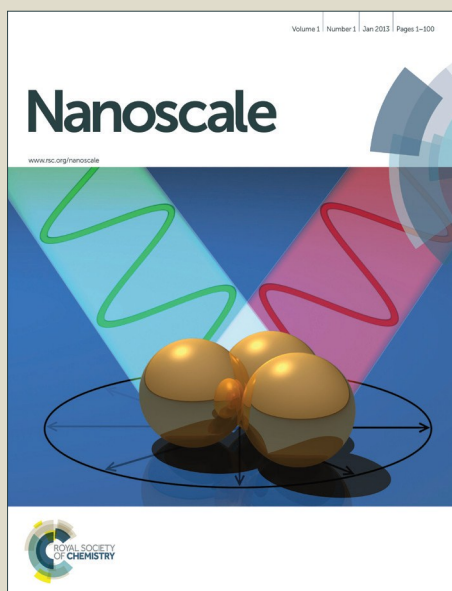
The user has requested enhancement of the downloaded file. All in-text references [underlined in blue](#) are added to the original document

Nanoscale

Accepted Manuscript



This article can be cited before page numbers have been issued, to do this please use: M. Hong, Z. G. Chen, L. Yang and J. Zou, *Nanoscale*, 2016, DOI: 10.1039/C6NR00719H.



This is an *Accepted Manuscript*, which has been through the Royal Society of Chemistry peer review process and has been accepted for publication.

Accepted Manuscripts are published online shortly after acceptance, before technical editing, formatting and proof reading. Using this free service, authors can make their results available to the community, in citable form, before we publish the edited article. We will replace this *Accepted Manuscript* with the edited and formatted *Advance Article* as soon as it is available.

You can find more information about *Accepted Manuscripts* in the [Information for Authors](#).

Please note that technical editing may introduce minor changes to the text and/or graphics, which may alter content. The journal's standard [Terms & Conditions](#) and the [Ethical guidelines](#) still apply. In no event shall the Royal Society of Chemistry be held responsible for any errors or omissions in this *Accepted Manuscript* or any consequences arising from the use of any information it contains.

Journal Name

ARTICLE

Enhancing Thermoelectric Performance of Bi₂Te₃-based Nanostructures through Rational Structure Design

 Received 00th January 20xx,
Accepted 00th January 20xx

DOI: 10.1039/x0xx00000x

www.rsc.org/

Min Hong^a, Zhi-Gang Chen^{*a}, Lei Yang^a and Jin Zou^{*ab}

Nanostructuring has been successfully employed to enhance the thermoelectric performance of Bi₂Te₃ due to their obtained low thermal conductivity. In order to further reduce the thermal conductivity, we design a hierarchical nanostructures assembled with well-aligned Bi₂Te₃ nanoplates using Te nanotubes as templates by a facial microwave-assisted solvothermal synthesis. From the comparisons of their thermoelectric performance and theoretical calculations with simple Bi₂Te₃ nanostructures, we found that Te/Bi₂Te₃ hierarchical nanostructures exhibits higher figure-of-merit due to the optimized reduced Fermi level and enhanced phonon scattering, as well as the suppressed bipolar conduction. This study provides an effective approach to enhance thermoelectric performance of Bi₂Te₃ based nanostructures by rationally designing the nanostructures.

Introduction

Considering the environmental pollution caused by the consumption of fossil fuels and the rising demand of energy depletion, it is necessary to develop green sustainable energy sources and energy harvesting technologies.¹ Thermoelectric materials, enabling the direct conversion between heat and electricity, provide an alternative solution to these crises.² The energy conversion efficiency of a thermoelectric material is gauged by the dimensionless figure of merit, $ZT = S^2\sigma T/\kappa$, where S , σ , κ and T are the Seebeck coefficient, electrical conductivity, thermal conductivity (including electronic component κ_e , lattice component κ_l , and bipolar component κ_{bi}), and the working temperature, respectively.³⁻⁵ However, the current low ZT values, especially for n-type (with free electrons) thermoelectric materials, significantly hinder the commercialization of thermoelectric devices, which demand the synergistic development of both n-type and p-type (with free holes) thermoelectric elements.^{6,7}

Bi₂Te₃ and the family of similar compounds are the promising thermoelectric candidates at room temperature region.⁸⁻¹⁰ Because of their six valley degeneracy, the narrow energy gap and layered crystal structure, Bi₂Te₃ potentially meets the criteria of high power factor ($S^2\sigma$) and low κ .¹¹ Compared with bulk counterpart, nanostructured Bi₂Te₃ can

achieve much lower κ , and provides promising possibilities to manipulate the thermoelectric properties.¹² Especially, rhombohedral structured Bi₂Te₃ nanoplates, as two-dimensional nanostructures,¹³⁻¹⁵ exhibit strengthened phonon scattering due to the dense grain boundaries after sintered into pellets.¹⁶ To further strengthen the phonon scattering, we can assemble the randomly orientated nanoplates in the form of well-aligned hierarchical nanostructures.¹⁷

Inspired by our previous study on epitaxial growth of T-shaped Te/Bi₂Te₃ heteronanojunctions,¹⁸ we explored the fabrication of the hierarchical nanostructures by using the one-dimensional Te nanostructures as templates. One-dimensional Te nanostructures, including nanowires¹⁹ and nanotubes^{20,21} have been reported to be synthesized by the wet chemical method. Compared with nanowires, nanotubes show even lower κ due to the existence of tube channels.²² Because of the potential lattice match between trigonal structured Te ($a_{Te} = 4.45 \text{ \AA}$, $c_{Te} = 5.92 \text{ \AA}$)²³ and rhombohedral structured Bi₂Te₃ ($a_{Bi_2Te_3} = 4.38 \text{ \AA}$, $c_{Bi_2Te_3} = 30.49 \text{ \AA}$)²⁴, i.e. $a_{Te} \approx a_{Bi_2Te_3}$, $c_{Te} \approx 1/5 c_{Bi_2Te_3}$, it is anticipated a small lattice mismatch of $\{11\bar{2}0\}$ plane for Te and Bi₂Te₃ (< 2%),²⁵ so that $\{11\bar{2}0\}$ planes of Te nanotubes can serve as templates for the epitaxial growth of Bi₂Te₃ nanoplates, as demonstrated in the atomic models of Te/Bi₂Te₃ heteronanojunctions (refer to Fig. 1a and b). Using this crystallographic relationship, Te/Bi₂Te₃ hierarchical nanostructures can be formed on Te nanostructures. For layered Bi₂Te₃ single crystals, κ is anisotropic and its value along the c -axis is only ~50% of that on the a - b plane,²⁶ so that massive studies have explored the advantage of well-aligned Bi₂Te₃ layered nanostructures to reduce κ .^{7,19,27} Therefore, this hierarchical nanostructures is expected to result in significantly

^a Materials Engineering, University of Queensland, Brisbane, QLD 4072, Australia.

^b Centre for Microscopy and Microanalysis, University of Queensland, Brisbane, QLD 4072, Australia.

Email: j.zou@uq.edu.au, z.chen1@uq.edu.au.

† Electronic Supplementary Information (ESI) available: XRD pattern, SEM, and TEM images of as-synthesized Te nanotubes. See DOI: 10.1039/x0xx00000x

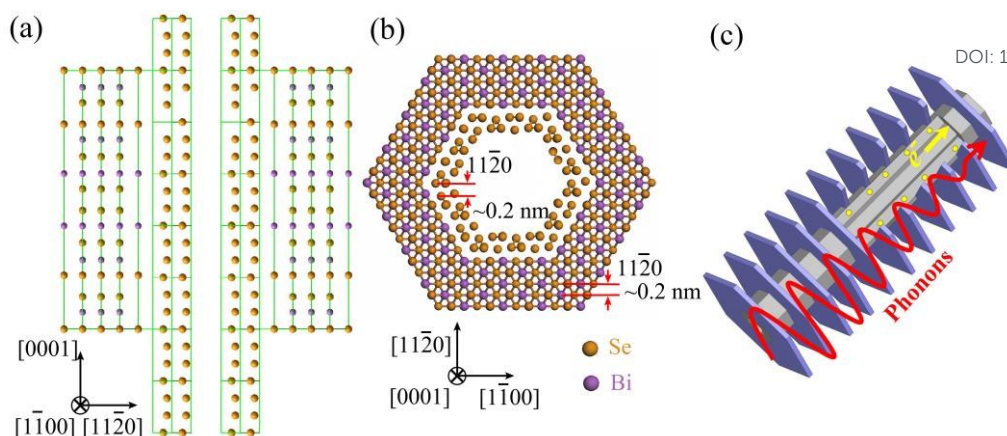
View Article Online
DOI: 10.1039/C6NR00719H

Fig. 1 Schematic atomic models for Te/Bi₂Te₃ hierarchical nanostructures showing the crystallographic relationship along (a) [1 $\bar{1}$ 00] and (b) [0001]. (c) Schematic demonstrating the advantages of the hierarchical nanostructure in strengthening phonon scattering and ensuring high electrical conductivity.

enhanced phonon scattering, as schematically illustrated in Fig. 1c. On the other hand, the crystalline nature of Te nanotube walls may enhance σ .^{22,28}

In this study, we employed a microwave-assisted solvothermal method to synthesize Te/Bi₂Te₃ hierarchical nanostructures using Te nanotubes as templates. To confirm the superiority of Te/Bi₂Te₃ hierarchical nanostructures in enhancing thermoelectric efficiency, highly uniform Bi₂Te₃ nanoplates were also investigated as a reference. Through the comparison of the morphology-dependent thermoelectric performance, we fundamentally studied the structural effects on tuning thermoelectric properties.

Experimental

Materials Synthesis and Processing

In this study, analytical grade Bi(NO₃)₃·5H₂O, Na₂TeO₃, ethylene glycol, poly(N-vinyl-2-pyrrolidone) (PVP, $M_w = 4000$), and NaOH solution were used as precursors.

The synthesis of the Te/Bi₂Te₃ hierarchical nanostructures was carried out in two steps. The first step is to synthesize Te nanotubes as the precursors, following by the second step - synthesis of Te/Bi₂Te₃ hierarchical nanostructures. In the first step, we added 332.4 mg Na₂TeO₃ and 0.2 g PVP into 40 mL ethylene glycol. The solutions were stirred vigorously for 30 min at room temperature. Subsequently, the obtained clear solutions were sealed in a 100 mL teflon vessel, which was heated in a CEM Mars-6 microwave oven at 230 °C for 5 min. After naturally cooled to room temperature, the as-synthesized Te nanotubes were collected by a high-speed centrifugation, washed six times with distilled water and absolute ethanol and finally dried at 60 °C for 12 h in a vacuum oven. In the second step, the obtained Te nanotubes were mixed with Bi(NO₃)₃·5H₂O into 40 mL ethylene glycol with a mole ratio of 2:3, and with NaOH solution (5 mol/L, 2 mL). After stirring for ~30 min, the mixed solution was transferred

into the teflon vessels again, and heated in the CEM Mars-6 microwave oven at 230 °C for 5 min. In the second step, NaOH with low concentration enables the gentle dissolution of Te from their external size walls to allow the epitaxial growth of Bi₂Te₃ nanoplates through the entire body of the Te nanotubes.²⁹ Through washing, centrifuging and drying, we obtained the final nanopowders.

As a comparison, pure Bi₂Te₃ nanoplates were also synthesized. During the synthesis, 485.1 mg Bi(NO₃)₃·5H₂O, 332.4 mg Na₂TeO₃ and 0.2 g PVP were mixed with 40 mL ethylene glycol and NaOH solution (5 mol/L, 2 mL). After being stirred vigorously, the obtained clear solutions were sealed in the teflon vessel, and heated in the CEM Mars-6 microwave oven at 230 °C for 5 min. After naturally cooled to room temperature, the synthesized products were collected by a high-speed centrifugation, washed six times with distilled water and absolute ethanol, and finally dried at 60 °C for at least 12 h in a vacuum oven.

Materials Characterizations

The phase purities of the as-synthesized products were examined by the X-ray diffractometer (XRD) equipped with graphite monochromatized, Cu $K\alpha$ radiation ($\lambda = 1.5418$ Å). The morphological, structural, and compositional characteristics of the synthesized products were investigated by scanning electron microscopy (SEM, JEOL 7800) and transition electron microscopy (TEM, FEI F20), equipped with EDS for compositional analysis.

Fabrication of Pellets

The as-synthesized Te/Bi₂Te₃ hierarchical nanostructures and Bi₂Te₃ nanoplates were compressed by the spark plasma sintering (SPS) under 40 MPa and at 250 °C for 5 min in vacuum into pellets with a diameter of 12.5 mm and a thickness of 2 mm. The densities (d) of sintered pellets were measured by an Archimedes method, and confirmed to be over 90%.

Thermoelectric Performance Measurement

Thermal diffusivity (D) of sintered pellets was measured by a laser flash method (LFA 457, NETZSCH), and κ was calculated through $\kappa = DC_p d$, where C_p is the specific heat capacity. C_p is obtained from empirical formulas $C_{pBT} = 108.06 + 5.53 \times 10^{-2} T$ $\text{JK}^{-1}\text{mol}^{-1}$ for Bi_2Te_3 .³⁰ σ and S were measured simultaneously on a ZEM-3, ULVAC. The uncertainties of the thermoelectric performance measurements (S , σ and D) were estimated as ~5% for each.

Results and discussion

Fig. 2a is the X-ray diffraction (XRD) pattern collected from the as-synthesized Te/ Bi_2Te_3 nanopowders with the inset showing its enlarged view of 2θ in the range of $34^\circ - 43^\circ$. As can be seen, the diffraction peaks can be indexed as the rhombohedral structured Bi_2Te_3 phase with lattice parameters of $a = 4.38 \text{ \AA}$ and $c = 30.49 \text{ \AA}$ (JCPDS No. 89-2009)²⁴ and the trigonal structured Te phase with lattice parameters of $a = 4.45 \text{ \AA}$ and $c = 5.92 \text{ \AA}$ (JCPDS No. 36-1452).²³ It should be noted that no Bi contamination was detected in the as-prepared samples, although our samples contain excessive Bi^{3+} (dissolved from $\text{Bi}(\text{NO}_3)_3 \cdot 5\text{H}_2\text{O}$). We believe that the excessive Bi^{3+} was still in the solvent after the synthesis that was washed away during the post-synthesis process. Fig. 2b is a SEM image, and shows that the majority (> 90%) of synthesized products

are rod-like nanostructures. Fig. 2c is a TEM image of a typical rod-like nanostructure, in which the feature of a hierarchical nanostructure is seen — many parallel nanoplates are linked by a nanotube (as a stem). Their crystallographic relationship was further analyzed using selected area electron diffraction (SAED) and high resolution TEM (HRTEM). Fig. 2d is a SAED pattern taken from the circled area of such hierarchical nanostructure showing superimposed $[1\bar{1}00]$ zone-axis diffraction patterns of a trigonal structured Te phase and a rhombohedral structured Bi_2Te_3 phase, from which the crystallographic relationship between the Te nanotube and the Bi_2Te_3 nanoplates can be determined as $[0001]_{\text{Te}} // [0001]_{\text{Bi}_2\text{Te}_3}$ and $[11\bar{2}0]_{\text{Te}} // [11\bar{2}0]_{\text{Bi}_2\text{Te}_3}$. Fig. 2e and f are the corresponding HRTEM images taken from the arrowed nanotube body and the nanoplate edge, respectively, which further suggests the coexistence of a high-crystalline trigonal structured Te nanotube stem and rhombohedral structured Bi_2Te_3 nanoplate. EDS was applied to examine the compositions of the nanotube and nanoplates. Fig. 2g shows the EDS profiles collected respectively from the labeled areas in Fig. 2c, suggesting that the nanotube is indeed Te, while the nanoplates are composed of Bi and Te with a mole ratio of approximately 2:3. To understand the structural characteristics of Te nanotubes after first step synthesis (an example is shown in the ESI), which demonstrated that the

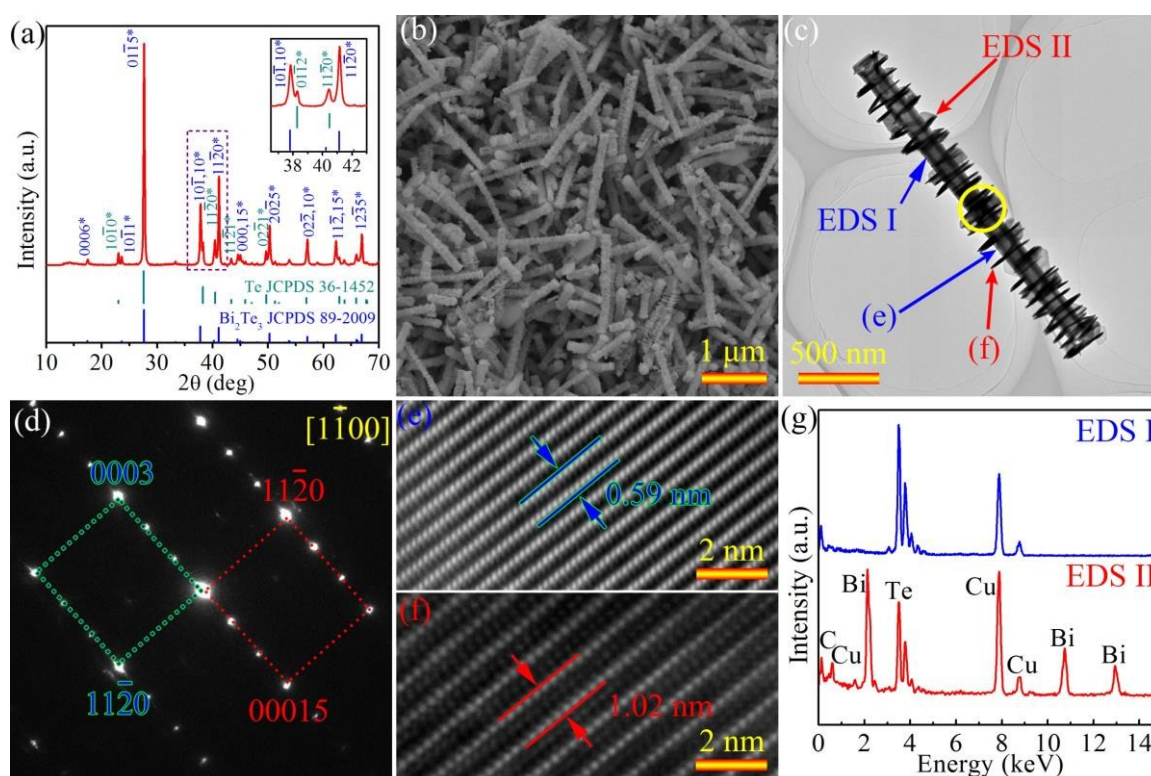


Fig. 2 (a) XRD patterns collected from as-synthesized Te/ Bi_2Te_3 nanopowders with inset showing its enlarged view. (b) Low-magnification SEM image showing a large amount of hierarchical nanostructures. (c) TEM image of a typical Te/ Bi_2Te_3 hierarchical nanostructure. (d) The $[1\bar{1}00]$ zone-axis SAED. (e) and (f) HRTEM images respectively taken from the arrowed areas in (c). (g) EDS profiles respectively taken from the arrowed areas in (c).

obtained nanotubes have their lengths of 2 - 6 μm and diameters of 100 - 200 nm. Our extensive electronic microscopy investigations of Te/Bi₂Te₃ hierarchical nanostructures indicate that the lateral size and thickness of the epitaxially grown Bi₂Te₃ nanoplates are relatively independent to the diameters of Te nanotubes.

As a comparison, Bi₂Te₃ nanoplates were also synthesized and characterized. Fig. 3a is a XRD pattern of as-prepared Bi₂Te₃ nanoplates, confirming Bi₂Te₃ nanoplates are highly pure rhombohedral structured Bi₂Te₃ phase. Fig. 3b is the low-magnification SEM image of as-synthesized Bi₂Te₃ hexagonal-shaped nanoplates that have uniform morphology with their lateral size of $\sim 1\mu\text{m}$. The inset of Fig. 3b is the high-magnification SEM image showing the side-view of several nanoplates, from which the nanoplate thickness of ~ 20 nm can be revealed. Fig. 3c is the TEM image of a typical nanoplate with lateral size of $\sim 1\mu\text{m}$, in accordance with the size determined by SEM (refer to Fig. 3b). Fig. 3d is the [0001] zone-axis SAED pattern and Fig. 3e is the corresponding HRTEM image with a lattice spacing of 0.22 nm, which matches well with the d value of the $\{11\bar{2}0\}$ planes of rhombohedral structured Bi₂Te₃.³¹ Fig. 3f shows the EDS profile, indicating that the elemental ratio of Bi and Te is approximately 2:3 (note that Cu and C peaks are caused by the TEM Cu grid with C supporting films).

In order to evaluate their thermoelectric performance, we examined sintered pellets made from Te/Bi₂Te₃ hierarchical nanostructures and Bi₂Te₃ nanoplates. Fig. 4a presents σ and S as a function of temperature, indicated by the left-hand side

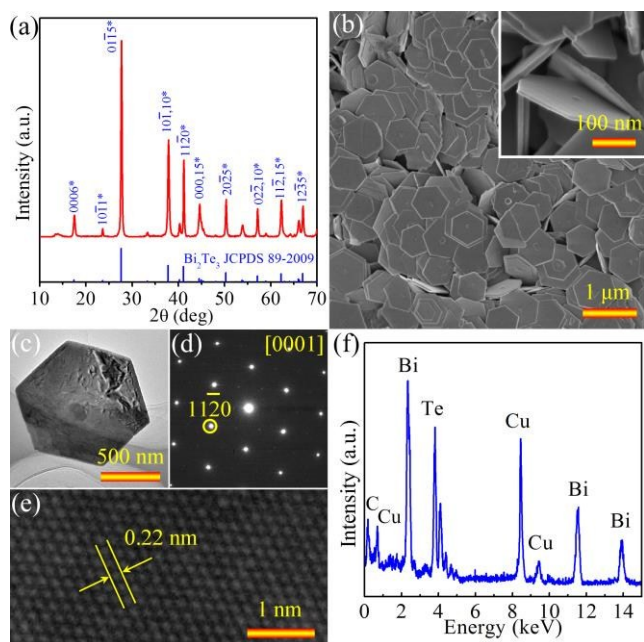


Fig. 3 (a) XRD pattern taken from the as-synthesized Bi₂Te₃ nanopowders (b) Low-magnification SEM image with inset of side-view high-magnification SEM image. (c) TEM image of a typical Bi₂Te₃ nanoplate. (d), (e), and (f) Corresponding SAED pattern, HRTEM image, and EDS profile, respectively.

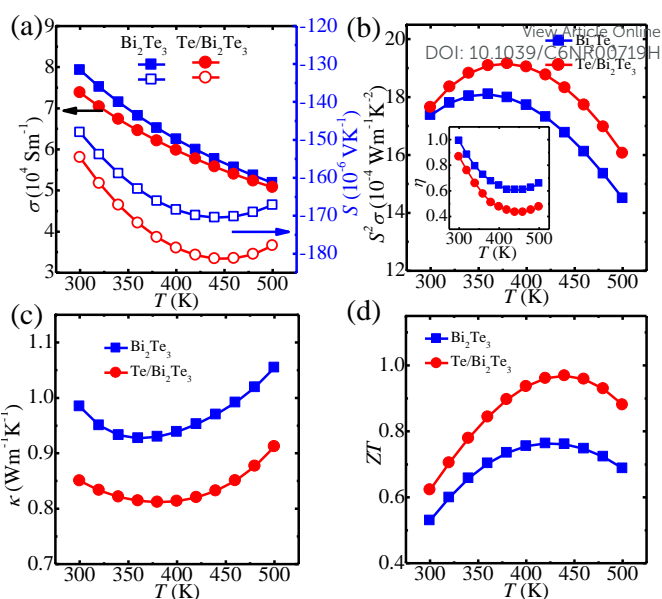


Fig. 4 Thermoelectric properties of Te/Bi₂Te₃ hierarchical nanostructures compared with Bi₂Te₃ nanoplates (a) σ and S , (b) $S^2\sigma$ with inset showing calculated η , (c) κ and (d) ZT .

and the right-hand side y-axis, respectively. As can be seen, σ declines from $\sim 8 \times 10^4 \text{ Sm}^{-1}$ to $\sim 5 \times 10^4 \text{ Sm}^{-1}$ with increasing the temperature for both Bi₂Te₃ and Te/Bi₂Te₃ based pellets; however the declining trend in Te/Bi₂Te₃ is mitigated. In the case of S , its negative sign for both Bi₂Te₃ and Te/Bi₂Te₃ cases indicates their n-type feature. Specifically, S for Bi₂Te₃ ranges from $-150 \mu\text{VK}^{-1}$ to $-170 \mu\text{VK}^{-1}$, while that for Te/Bi₂Te₃ fluctuates between $-165 \mu\text{VK}^{-1}$ and $-182 \mu\text{VK}^{-1}$ in the studied temperature range. Moreover, the absolute value of S increases first and then decreases with increasing the temperature. The decrease in $|S|$ should be caused by the bipolar conduction,³² and the peak of $|S|$ for Te/Bi₂Te₃ shifts towards the higher temperature, suggesting that the bipolar conduction is suppressed at the higher temperature. Based on the measured σ and S , we can calculate $S^2\sigma$, and plotted in Fig. 4b as a function of temperature. As can be seen, the peak $S^2\sigma$ of $19.2 \times 10^{-4} \text{ Wm}^{-1}\text{K}^{-2}$ for Te/Bi₂Te₃ is larger than that of $18 \times 10^{-4} \text{ Wm}^{-1}\text{K}^{-2}$ for Bi₂Te₃, and the peak $S^2\sigma$ for Te/Bi₂Te₃ shifts to higher temperature. This is due to the suppressed bipolar conduction and the mitigated declining trend in σ with increasing the temperature in Te/Bi₂Te₃ (refer to Fig. 4a).

To understand the enhanced $S^2\sigma$, we calculated the reduced Fermi level ($\eta = E_f/k_B T$, with E_f representing the Fermi level and k_B is the Boltzmann constant) based on the measured S by using the following equation³³

$$S = -\frac{k_B}{e} \left[\frac{2F_1(\eta)}{F_0(\eta)} - \eta \right], \quad (1)$$

with the generalized Fermi integral

$$F_i(\eta) = \int_0^\infty \frac{\varepsilon^i}{1 + \exp(\varepsilon - \eta)} d\varepsilon; \quad (2)$$

where e is the elementary charge. The inset of Fig. 4b plots the variation of η with temperature for both Bi₂Te₃ and Te/Bi₂Te₃

in which η for Te/Bi₂Te₃ is smaller than that for Bi₂Te₃. According to our previous study,³⁴ to maximize $S^2\sigma$, the Fermi level should locate near the conduction band edge for n-type thermoelectric materials. Compared with Bi₂Te₃, η for Te/Bi₂Te₃ is closer to its conduction band edge, so that an enhanced $S^2\sigma$ for Te/Bi₂Te₃ can be anticipated. The η decline for Te/Bi₂Te₃ nanostructures can be ascribed to the excessive Te (provided by Te nanotube stems), which might suppress the Te vacancies in epitaxially grown Bi₂Te₃ nanoplates. Te vacancies in Bi₂Te₃ are generally unavoidable (giving n-type transport feature), and the Te vacancies lead to the Fermi level residing deep in the conduction band. Favourably, by adding more Te, Te vacancies in Bi₂Te₃ can be suppressed; resulting in the shift of the Fermi level towards the valence band in our Te/Bi₂Te₃ nanostructures. Fig. 4c plots κ versus temperature, from which κ in Te/Bi₂Te₃ shows ~20% reduction than that for Bi₂Te₃. Due to the enlarged $S^2\sigma$ and simultaneously decreased κ , ZT for Te/Bi₂Te₃ is enhanced, as shown in Fig. 4d. ZT for Te/Bi₂Te₃ reaches ~1, much larger than that of ~0.75 for Bi₂Te₃.

From above discussion, one of the critical reasons for enhanced ZT is the significantly decreased κ . To clarify the underlying principle, we studied the contributions of κ from electrons, phonons and bipolar conduction. According to the Wiedemann-Franz law,³⁵ κ_e can be expressed as

$$\kappa_e = L\sigma T, \quad (3)$$

where L is the Lorenz number. Employing the single Kane band model, L can be determined by³⁶

$$L = \left(\frac{k_B}{e}\right)^2 \left[\frac{3F_2(\eta)}{F_0(\eta)} - \left(\frac{2F_2(\eta)}{F_0(\eta)}\right)^2 \right] \quad (4)$$

Through inputting the determined η (refer to the inset of Fig. 4b) into Equation (4), we can calculate L . The results are shown in Fig. 5a, in which L fluctuates around $1.6 \times 10^{-8} \text{ V}^2 \text{ K}^{-2}$ for both samples, matching with reported values for nanostructured thermoelectric systems.³⁷ On this basis, Fig. 5b plots the calculated κ_e over the studied temperature, where κ_e is reduced in Te/Bi₂Te₃ due to its smaller σ and L over Bi₂Te₃. By subtracting κ_e from κ , we can study the variation of κ_l , although there is a κ_{bi} contribution at high temperature. Fig. 4b shows the obtained temperature dependent $\kappa - \kappa_e$, which suggests that κ_l in Te/Bi₂Te₃ is significantly decreased. This is because Te/Bi₂Te₃ hierarchical nanostructures have the well-aligned nanoplates attached on the body surface, which lead to stronger phonon scattering compared with the randomly orientated Bi₂Te₃ nanoplates.³⁸ Moreover, κ_{bi} is calculated using the reference-outlined method.³⁹ Specifically, by extrapolating the linear relationship between κ_l and $1/T$ demonstrated in the inset of Fig. 5c, we can obtain κ_l in the entire studied temperature range, and finally, though subtracting κ_l from $\kappa - \kappa_e$, we can obtain κ_{bi} . Fig. 5d shows the determined κ_{bi} as a function of temperature. As can be seen, κ_{bi} for Te/Bi₂Te₃ is reduced; suggesting that the bipolar conduction in Te/Bi₂Te₃ has been indeed suppressed, which is consistent with the peak of S for Te/Bi₂Te₃ shifting to the high temperature (refer to Fig. 4a). To understand this, we note that the band gap difference between Te (0.33 eV)⁴⁰ and Bi₂Te₃

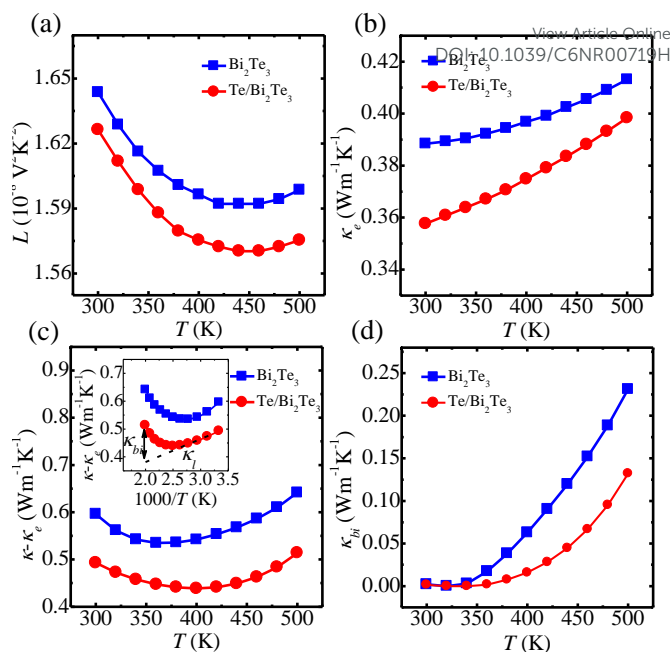


Fig. 5 (a) Calculated temperature dependent (a) L , (b) κ_e , (c) $\kappa - \kappa_e$ with inset showing the inverse temperature dependence of $\kappa - \kappa_e$, and (d) κ_{bi} .

(0.15 eV)⁴¹ may lead to an extra energy offset between the conduction and valence bands for the Te/Bi₂Te₃ nanostructures. In addition, our Bi₂Te₃ nanoplates in Te/Bi₂Te₃ are generally thinner than the normal Bi₂Te₃ nanoplates, leading to the enlargement of band gap in our thinner Bi₂Te₃ nanoplates.⁴² As a consequence, the bipolar conduction can be suppressed in our Te/Bi₂Te₃ nanostructures.

Conclusion

We successfully fabricated Te/Bi₂Te₃ hierarchical nanostructures using Te nanotubes as templates by the facial microwave-assisted solvothermal method. Through systematic morphological, structural and compositional characterizations, structural quality and the epitaxial growth of well-aligned Bi₂Te₃ nanoplates on Te nanotube stems are verified. The thermoelectric properties measured from their sintered pellets indicate an increased $ZT \approx 1$ when compared with their pure Bi₂Te₃ nanoplates with $ZT \approx 0.75$. Our modelling studies suggest that the enhanced ZT of our Te/Bi₂Te₃ hierarchical nanostructures is caused by the optimized reduced Fermi level, the strengthened phonon scatterings, and the suppressed bipolar conduction. This study provides an effective approach to enhance thermoelectric efficiency by designing rational nanostructures.

Acknowledgements

This work was financially supported by the Australian Research Council. MH thanks the China Scholarship Council for providing a PhD stipend. The Australian Microscopy & Microanalysis

Research Facility is acknowledged for providing characterization facilities.

Notes and references

1. T. M. Tritt and M. A. Subramanian, *Mrs. Bull.*, 2006, **31**, 188-194.
2. G. J. Snyder and E. S. Toberer, *Nat. Mater.*, 2008, **7**, 105-114.
3. Z.-G. Chen, G. Han, L. Yang, L. Cheng and J. Zou, *Prog. Nat. Sci.*, 2012, **22**, 535-549.
4. L. Yang, Z.-G. Chen, G. Han, M. Hong, Y. Zou and J. Zou, *Nano Energy*, 2015, **16**, 367-374.
5. G. Han, Z.-G. Chen, L. Yang, M. Hong, J. Drennan and J. Zou, *ACS Appl. Mater. Interf.*, 2014, **7**, 989-995.
6. F. J. DiSalvo, *Science*, 1999, **285**, 703-706.
7. H.-C. Chang, C.-H. Chen and Y.-K. Kuo, *Nanoscale*, 2013, **5**, 7017-7025.
8. B. Poudel, Q. Hao, Y. Ma, Y. Lan, A. Minnich, B. Yu, X. Yan, D. Wang, A. Muto, D. Vashaee, X. Chen, J. Liu, M. S. Dresselhaus, G. Chen and Z. Ren, *Science*, 2008, **320**, 634-638.
9. R. J. Mehta, Y. Zhang, C. Karthik, B. Singh, R. W. Siegel, T. Borca-Tasciuc and G. Ramanath, *Nat. Mater.*, 2012, **11**, 233-240.
10. M. Hong, Z. G. Chen, L. Yang and J. Zou, *Nano Energy*, 2016, **20**, 144-155.
11. D. M. Rowe, *CRC handbook of thermoelectrics*, CRC Press, New York, 1995.
12. S. W. Finefrock, H. Yang, H. Fang and Y. Wu, *Annu. Rev. Chem. Biomol. Eng.*, 2015, **6**, null.
13. Y. Zhang, L. P. Hu, T. J. Zhu, J. Xie and X. B. Zhao, *Cryst. Growth Des.*, 2013, **13**, 645-651.
14. H.-W. Tsai, T.-H. Wang, T.-C. Chan, P.-J. Chen, C.-C. Chung, A. Yaghoubi, C.-N. Liao, E. W.-G. Diau and Y.-L. Chueh, *Nanoscale*, 2014, **6**, 7780-7785.
15. L. Guo, H. Yan, Q. Moore, M. Buettner, J. Song, L. Li, P. T. Araujo and H.-T. Wang, *Nanoscale*, 2015, **7**, 11915-11921.
16. A. Soni, Y. Shen, M. Yin, Y. Zhao, L. Yu, X. Hu, Z. Dong, K. A. Khor, M. S. Dresselhaus and Q. Xiong, *Nano Lett.*, 2012, **12**, 4305-4310.
17. W. G. Lu, Y. Ding, Y. X. Chen, Z. L. Wang and J. Y. Fang, *J. Am. Chem. Soc.*, 2005, **127**, 10112-10116.
18. L. Cheng, Z.-G. Chen, L. Yang, G. Han, H.-Y. Xu, G. J. Snyder, G.-Q. Lu and J. Zou, *J. Phys. Chem. C*, 2013, **117**, 12458-12464.
19. H. Fang and Y. Wu, *J. Mater. Chem. A*, 2014, **2**, 6004-6014.
20. B. Mayers and Y. Xia, *Adv. Mater.*, 2002, **14**, 279-282.
21. B. Kim and B.-K. Park, *Electronic Materials Letters*, 2012, **8**, 33-36.
22. D. M. Rowe, *Thermoelectrics Handbook : Macro to Nano*, CRC Press, Hoboken, 2005.
23. J.-M. Song, Y.-Z. Lin, Y.-J. Zhan, Y.-C. Tian, G. Liu and S.-H. Yu, *Cryst. Growth Des.*, 2008, **8**, 1902-1908.
24. S. Nakajima, *J. Phys. Chem. Solids*, 1963, **24**, 479-485.
25. J. L. Mi, N. Lock, T. Sun, M. Christensen, M. Sondergaard, P. Hald, H. H. Hng, J. Ma and B. B. Iversen, *ACS Nano*, 2010, **4**, 2523-2530.
26. M. Carle, P. Pierrat, C. Lahalle-Gravier, S. Scherrer and H. Scherrer, *J. Phys. Chem. Solids*, 1995, **56**, 201-209.
27. W. Shi, S. Yu, P. Liu and W. Fan, *CrystEngComm*, 2013, **15**, 2978-2985.
28. W. Liu, X. Yan, G. Chen and Z. Ren, *Nano Energy*, 2012, **1**, 42-56.
29. Y. Liang, W. Wang, B. Zeng, G. Zhang, Q. He and J. Fu, *Mater. Chem. Phys.*, 2011, **129**, 90-98.
30. K. C. Mills, *Thermodynamic Data for Inorganic Sulphides, Selenides and Tellurides*, Butterworths, London, 1974.
31. L. Cheng, Z.-G. Chen, S. Ma, Z.-D. Zhang, Y. Wang, H.-Y. Xu, L. Yang, G. Han, K. Jack, G. Lu and J. Zou, *J. Am. Chem. Soc.*, 2012, **134**, 18920-18923.
32. S. Wang, G. Tan, W. Xie, G. Zheng, H. Li, J. Yang and X. Tang, *J. Mater. Chem.*, 2012, **22**, 20943-20951.
33. C. L. Chen, H. Wang, Y. Y. Chen, T. Day and G. J. Snyder, *J. Mater. Chem. A*, 2014, **2**, 11171-11176.
34. M. Hong, Z.-G. Chen, L. Yang, G. Han and J. Zou, *Adv. Electron. Mater.*, 2015, **1**, 1500025.
35. J. R. Sootsman, D. Y. Chung and M. G. Kanatzidis, *Angew. Chem. Int. Edit.*, 2009, **48**, 8616-8639.
36. T. Zhu, H. Gao, Y. Chen and X. Zhao, *J. Mater. Chem. A*, 2014, **2**, 3251-3256.
37. L. Zhao, S. H. Lo, J. He, H. Li, K. Biswas, J. Androulakis, C.-I. Wu, T. P. Hogan, D.-Y. Chung, V. P. Dravid and M. G. Kanatzidis, *J. Am. Chem. Soc.*, 2011, **133**, 20476-20487.
38. X. B. Zhao, X. H. Ji, Y. H. Zhang, T. J. Zhu, J. P. Tu and X. B. Zhang, *Appl. Phys. Lett.*, 2005, **86**.
39. W.-S. Liu, B.-P. Zhang, J.-F. Li, H.-L. Zhang and L.-D. Zhao, *J. Appl. Phys.*, 2007, **102**, 103717.
40. V. B. Anzin, M. I. Eremets, Y. V. Kosichkin, A. I. Nadezhdinskii and A. M. Shirokov, *Phys. Status Solidi A*, 1977, **42**, 385-390.
41. D. L. Greenaway and G. Harbeke, *J. Phys. Chem. Solids*, 1965, **26**, 1585-1604.
42. O. V. Yazyev, J. E. Moore and S. G. Louie, *Phys. Rev. Lett.*, 2010, **105**, 266806.

Journal Name

ARTICLE

TOC

Enhancing Thermoelectric Performance of Bi_2Te_3 -based Nanostructures through Rational Structure Design

Min Hong^a, Zhi-Gang Chen^{*a}, Lei Yang^a and Jin Zou^{*ab}

Enhanced thermoelectric performance in $\text{Te}/\text{Bi}_2\text{Te}_3$ hierarchical nanostructures caused by strengthened phonon scattering, optimized Fermi level, and suppressed bipolar conduction

